CNA1302K (ON1004)

Photo Interrupter

For contactless SW and object detection

Overview

CNA1302K is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

Features

• Ultraminiature: 4.2 mm × 5.0 mm (height: 5.2 mm)

• Fast response: t_r , $t_f = 35 \mu s$ (typ.)

• Highly precise position detection: 0.15 mm

• Gap width: 2.0 mm

■ Absolute Maximum Ratings $T_a = 25$ °C

F	Symbol	Rating	Unit	
Input (Light emitting diode)	Power dissipation *1	P_{D}	75	mW
	Forward current	I_{F}	50	mA
	Reverse voltage	V_R	6	V
Output (Photo transistor)	Collector-emitter voltage (Base open)	Vone		V
	Emitter-collector voltage (Base open)	V _{ECO}	6	V
	Collector current	I_{C}	20	mA
	Collector power dissipation *2	$P_{\rm C}$	75	mW
Operating ambient temp	T _{opr}	-25 to +85	°C	
Storage temperature	T _{stg}	-40 to +100	°C	

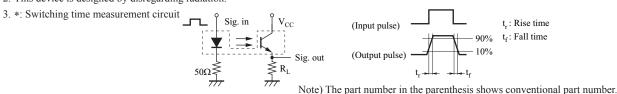
Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C

■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

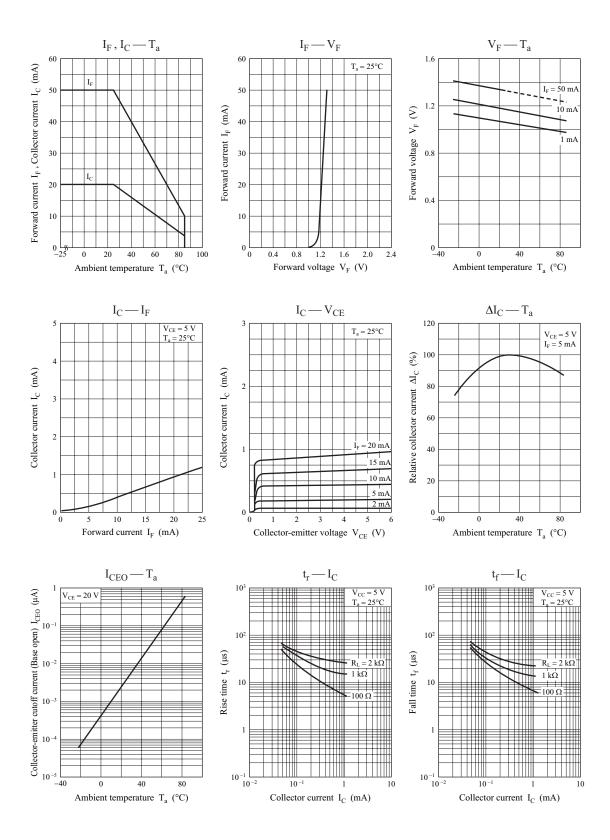
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3 V$			10	μΑ
	Forward voltage	V _F	$I_F = 20 \text{ mA}$		1.2	1.4	V
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = 20 \text{ V}$			100	nA
Transfer characteristics	Collector current	I_{C}	$V_{CE} = 5 \text{ V}, I_F = 5 \text{ mA}$	40		400	μА
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 10 \text{ mA}, I_C = 40 \mu\text{A}$			0.4	V
	Rise time *	t _r	$V_{CC} = 5 \text{ V}, I_C = 0.1 \text{ mA},$		35		μs
	Fall time *	$t_{\rm f}$	$R_{\rm L} = 1000\Omega$		35		μs

Note) 1. Input and output are practiced by electricity.

2. This device is designed by disregarding radiation.

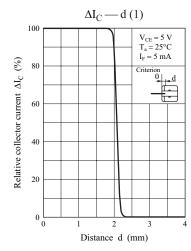


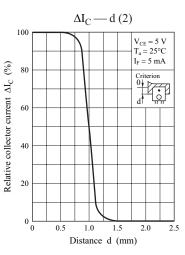
^{*2:} Output power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C



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Panasonic CNA1302K

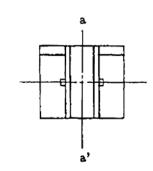


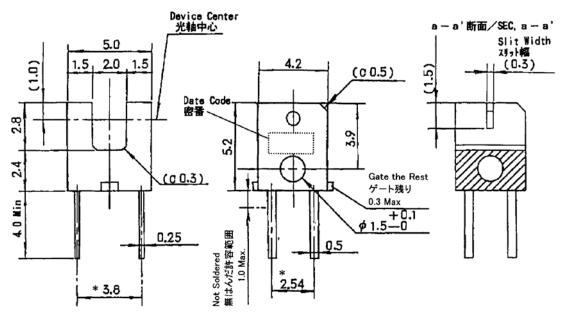


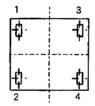
Panasonic

■ Package (Unit: mm)

LSMSIN4S0005







- (注 1)(Note1) * リード根元寸法とします/ * Indicates root dimensions of lead.
- (注 2)(Note2)指示無き寸法公差は±0.2/Not appointment tolerance :±0.2
- (注 3)(Note3)パリ寸法は 0.15 Max./Barri measure : 0.15 Max.
- (注 4) 上記寸法は、バリ・ゲート残り等を含んでおりません

(Note4)An aforementioned dimension doesn't include projects and gate the rest remainder.

(注 5) 密番は、目視又は顕微鏡に於いて解読できる事

(Note5)What a date code sees an attention and can decode in a microscope.

- Pin name
 - 1: Anode
 - 2: Cathode
 - 3: Collector
 - 4: Emitter

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